



Low Capacitance TVS/ESD Protection Diodes

ESD PROTECTION DIODES

DESCRIPTION

ESD1201OC is a low-capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for data, control or power lines. With maximum capacitance of 15pF only, ESD1201OC is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 (±15kV air, ±8kV contact discharge), very fast charged device model (CDM) ESD and cable discharge event (CDE),etc. ESD1201OC uses ultra-small DFN1006 package. Each ESD1201OC device can protect one data line. It offers system designers flexibility to protect single data line where space is a premium concern..

Features

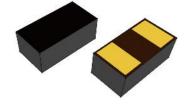
- ♦ Peak Power Dissipation 150 W (8/20µs)
- Stand-off voltag:12V
- Low capacitance 15pF(Maximum)
- ◆ Protects I/O Port
- Low clamping voltage
- ◆ Low Leakage
- Low Capacitance
- ◆ Response Time is <1ns</p>
- Meets MSL 1 Requirements
- Replacement for MLV(0402)

Applications

- Cell Phone Handsets and Accessories
- Serial and Parallel Ports
- Projection TV
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Peripherals
- MP3 Players

Pin Configuration





Circuit Diagram



Mechanical Characteristics

◆ Package: DFN1006

◆ Flammability Rating: UL 94V-0

◆ High temperature soldering guaranted: 260°C/10s

◆ Marking: MOC

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	± 25 ± 20	kV
Peak Pulse Power(tp=8/20us waveform)	P _{PP}	150	W
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

The above data are for reference only.



ESD12010C

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Electrical Characteristics (TA=25°C unless otherwise specified)

Symbol	Param	Test Condition	Min	Тур	Max	Units
V_{RWM}	Reverse Working Voltage				12.0	٧
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA	13.3			V
I _R	Reverse Leakage Current	$V_{RWM} = 12V$			0.2	μΑ
V _C	Clamping Voltage	$I_{PP} = 1A, t_p = 8/20 \mu s$			19	V
		$I_{PP} = 5A, t_p = 8/20 \mu s$			26	V
CJ	Junction Capacitance	V _R = 0V, f = 1MHz		13	15	pF

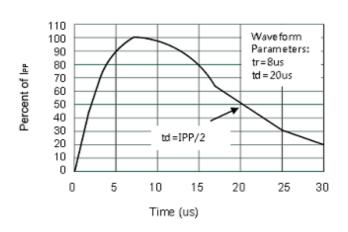
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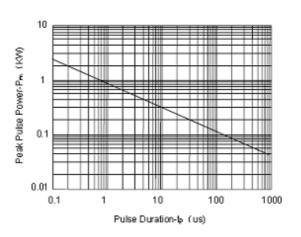




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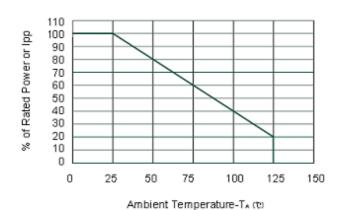
ELECTRICAL CHARACTERISTICS CURVE





Pulse Waveform

Non-Repetitive Peak Pulse Power vs. Pulse Time



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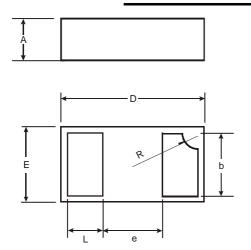




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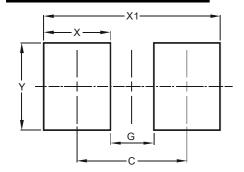
Outlitne Drawing

DFN1006 Package Outline Dimensions



DFN1006					
Dim	Min	Max	Тур		
Α	0.45	0.55	0.50		
b	0.45	0.55	0.50		
D	0.95	1.05	1.00		
E	0.55	0.65	0.60		
е	-	-	0.40		
L	0.20	0.30	0.25		
R	0.07	0.17	0.12		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)		
С	0.90		
G	0.40		
X	0.50		
X1	1.10		
Y	0.50		

Note:

- 1.Controlling dimension:in/millimeters.
- 2.General tolerance: ±0.05mm.
- 3. The pad layout is for reference purposes only.

PACKAGE SPECIFICATIONS

Package	Reel Size	Reel DIA. (mm)	Q'TY/Reel (pcs)	Box Size (mm)	QTY/Box (pcs)	Carton Size (mm)	Q'TY/Carton (pcs)
DFN1006	7'	178	10,000	210×210×205	100,000	445×445×230	400,000

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